Rectifier diodes schottky barrier

PBYR225CT series

GENERAL DESCRIPTION

Dual nickel silicide schottky barrier rectifier diodes in a plastic énvelope suitable for surface mounting, featuring low forward voltage drop and absence of stored charge. These devices can withstand reverse and voltage transients have guaranteed reverse surge capability. The devices are intended for use in switched mode power supplies and d.c. to d.c. converters, or as or-ing diodes in fault tolerant power supply systems.

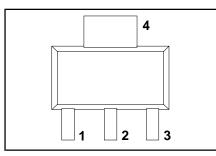
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
V _{RRM} V _F I _{O(AV)}	PBYR2- Repetitive peak reverse voltage Forward voltage Output current (both diodes conducting)	20CT 20 0.33 2	25CT 25 0.33 2	V V A

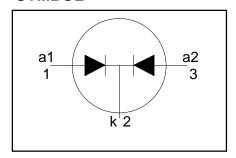
PINNING - SOT223

PIN	DESCRIPTION
1	anode 1 (a)
2	cathode (k)
3	anode 2 (a)
4	cathode (k)

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MA	λX.	UNIT
V _{RRM} V _{RWM} V _R	Repetitive peak reverse voltage Crest working reverse voltage Continuous reverse voltage	T _{sp} ≤ 97 °C	1 1 1	-20 20 20 20	-25 25 25 25	<<<
I _{O(AV)}	Output current (both diodes conducting)	square wave; $\delta = 0.5$; $T_{sp} \le 136$ °C	-	2	2	Α
I _{O(RMS)} I _{FRM}	RMS forward current Repetitive forward peak current per diode	$t = 25\mu s; \delta = 0.5; T_{sp} \le 136 °C$	-	2. 2	8	A A
I _{FSM}	Non-repetitive peak forward current per diode.	t = 10 ms t = 8.3 ms sinusoidal $T_j = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{\text{RWM(max)}}$	-	6.	6 6	A A
l ² t	I ² t for fusing	t = 10 ms	-	0.	18	A ² s
I _{RRM}	Repetitive peak reverse current per diode.	$t_p = 2 \ \mu s; \ \delta = 0.001$	-	1		Α
I _{RSM}	Non-repetitive peak reverse current per diode.	$t_p = 100 \ \mu s$	-	1		Α
${\mathsf T}_{stg} \atop {\mathsf T}_{\mathsf j}$	Storage temperature Operating junction temperature		-40 -	15 15	-	ο̈́ς

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-sp}	Thermal resistance junction to solder point	one or both diodes conducting	-	-	17	K/W
R _{th j-a}		pcb mounted; minimum footprint pcb mounted; pad area as in fig:6		156 70	-	K/W K/W

STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	Forward voltage (per diode)	I _F = 1 A; T _j = 125°C I _F = 2 A	-	0.28	0.33	V
,	,	$I_{\rm F} = 2 \text{A}$	-	0.42	0.51	V
I _R	Reverse current (per diode)	$V_{p} = V_{p_{MM}}$	-	0.05	3	mA
	,	$V_{R} = V_{RWM}$; $T_{i} = 100 ^{\circ}C$	-	5	10	mA
l C _d	Junction capacitance (per	$V_{R} = V_{RWM}^{(VWW)}; T_{j} = 100 ^{\circ}C$ $f = 1MHz; V_{R} = 5V; T_{j} = 25 ^{\circ}C to$	-	160	-	pF
	diode)	125 °C				

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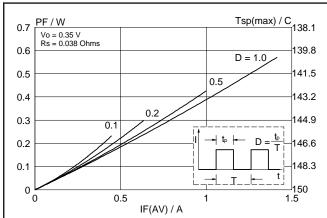


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; square current waveform where $I_{F(AV)} = I_{F(RMS)} x \sqrt{D}$.

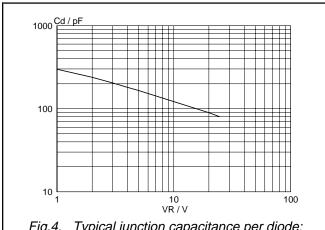


Fig.4. Typical junction capacitance per diode; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25$ °C to 125 °C.

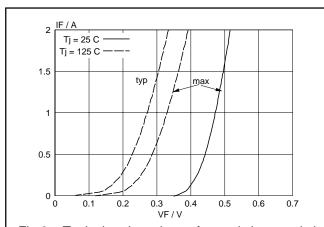


Fig.2. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_j

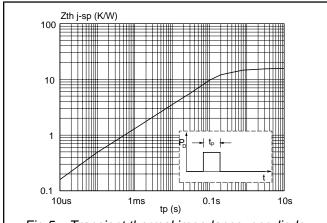


Fig.5. Transient thermal impedance; per diode; $Z_{th j ext{-}sp} = f(t_p)$.

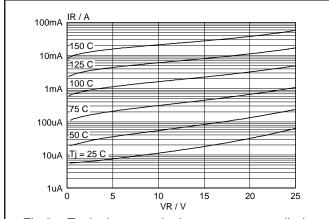
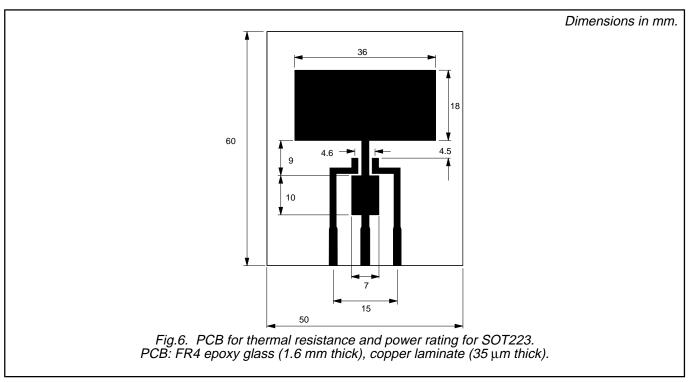


Fig.3. Typical reverse leakage current per diode; $I_R = f(V_R)$; parameter T_j

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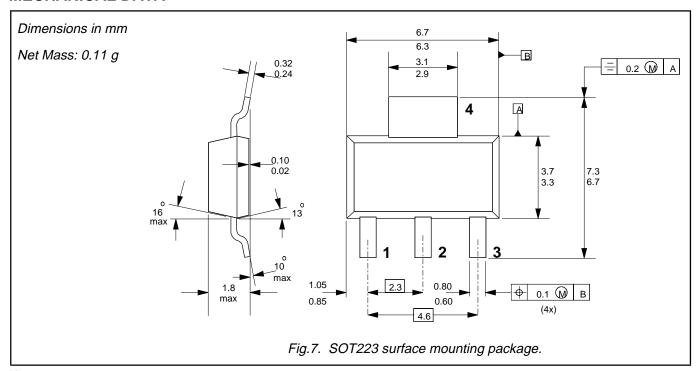
PRINTED CIRCUIT BOARD



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MECHANICAL DATA



Notes

- For further information, refer to Philips publication SC18 " SMD Footprint Design and Soldering Guidelines".
 Order code: 9397 750 00505.
 Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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